

# HiPerRF™ Power MOSFETs

IXFH 60N20F IXFT 60N20F  $V_{DSS}$  = 200V  $I_{D25}$  = 60A  $R_{DS(an)}$  = 38m $\Omega$ 

t<sub>rr</sub> ≤ 200 ns

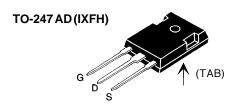
F-Class: MegaHertz Switching

N-Channel Enhancement Mode Avalanche Rated, Low  $\mathbf{Q_g}$ , Low Intrinsic  $\mathbf{R_g}$  High dV/dt, Low  $\mathbf{t_{rr}}$ 

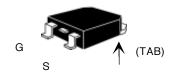


Symbol	Test Conditions	Maximun	n Ratings
V <sub>DSS</sub>	T <sub>1</sub> = 25°C to 150°C	200	V
V <sub>DGR</sub>	$T_J^J = 25^{\circ}C$ to 150°C; $R_{GS} = 1 M\Omega$	200	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	60	Α
I <sub>DM</sub>	$T_{c}^{\circ}$ = 25°C, pulse width limited by T <sub>1</sub>	м 240	Α
I <sub>AR</sub>	$T_{\rm c}$ = 25°C	60	Α
E <sub>AR</sub>	T <sub>C</sub> = 25°C	35	mJ
E <sub>AS</sub>	$T_{\rm c}^{\circ} = 25^{\circ}{\rm C}$	1.5	J
dv/dt	$I_{S} \leq I_{DM},  di/dt \leq 100   A/\mu s,  V_{DD} \leq V_{DS}$ $T_{J} \leq 150  ^{\circ}C,  R_{G} = 2  \Omega$	s 10	V/ns
P <sub>D</sub>	$T_{\rm C} = 25^{\circ} C$	315	W
T <sub>J</sub>		-55 +150	°C
$T_{JM}$		150	°C
T <sub>stg</sub>		-55 +150	°C
$\overline{T_{L}}$	1.6 mm (0.063 in.) from case for 10 s	300	°C
M <sub>d</sub>	Mounting torque TO-247	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
-	TO-268	4	g

	TO-268			4 g
Symbol	Test Conditions	Ch (T <sub>J</sub> = 25°C, unless		ristic Values se specified)
		min.	typ.	max.
V <sub>DSS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = 1 \text{mA}$	200		V
V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_{D} = 4mA$	2.0		4.0 V
I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$			±100 nA
I <sub>DSS</sub>	$V_{DS} = V_{DSS}$			50 μΑ
	$V_{GS}^{DS} = 0 \text{ V}$	$T_J = 125^{\circ}C$		1.5 mA
R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_{D} = 0.5 I_{D25}$ Note 1			38 mΩ



# TO-268 (IXFT) Case Style



G = Gate, D = Drain, S = Source, TAB = Drain

### **Features**

- RF capable MOSFETs
- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- Fast intrinsic rectifier

### **Applications**

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- 13.5 MHz industrial applications
- Pulse generation
- Laser drivers
- RF amplifiers

# **Advantages**

- Space savings
- High power density



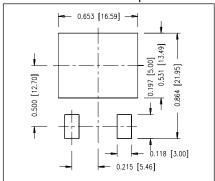
Symbol	<b>Test Conditions</b>	Characteristic Values (T <sub>1</sub> = 25°C, unless otherwise specified)				
			min.	typ.	max.	
9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}; I_{D} = 0.5 I_{D25}$	Note 1	18	26		S
$C_{iss}$	)			2930		pF
C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, t$	f = 1 MHz		940		pF
C <sub>rss</sub>	J			320		pF
t <sub>d(on)</sub>	)			15		ns
t <sub>r</sub>	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5$	$V_{DSS}$ , $I_{D} = 0.5$	I <sub>D25</sub>	14		ns
$\mathbf{t}_{d(off)}$	$R_G = 2.0 \Omega$ (External)			42		ns
t <sub>f</sub>	J			7.0		ns
Q <sub>g(on)</sub>	)			100		nC
$\mathbf{Q}_{gs}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5$	$V_{DSS}$ , $I_{D} = 0.5$	I <sub>D25</sub>	25		nC
$\mathbf{Q}_{gd}$	J			46		nC
R <sub>thJC</sub>					0.39	K/W
R <sub>thCK</sub>	(TO-247)			0.25		K/W

### Source-Drain Diode

Symbol	Test Conditions min.	typ.	max.	
I <sub>s</sub>	$V_{GS} = 0 V$		60	Α
I <sub>SM</sub>	Repetitive; pulse width limited by $T_{_{JM}}$		240	Α
V <sub>SD</sub>	$I_F = I_S$ , $V_{GS} = 0$ V, Note 1		1.5	V
t <sub>rr</sub>	)		200	ns
$\mathbf{Q}_{RM}$	$I_F = 25A, -di/dt = 100 A/\mu s, V_R = 100 V$	0.8		μС
I <sub>RM</sub>	J	10		Α

Note: 1. Pulse test,  $t \le 300 \mu s$ , duty cycle  $d \le 2 \%$ 

# Min Recommended Footprint

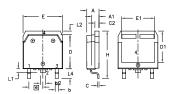


IXYS reserves the right to change limits, test conditions, and dimensions.

# TO-247 AD Outline Terminals: 1 - Gate 2 - Drain 3 - Source Tab - Drain

Dim.	Millimeter		Inc	hes
	Min.	Max.	Min.	Max.
Α	4.7	5.3	.185	.209
A,	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
С	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
е	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

### TO-268 Outline





Dim.	Millimeter		Millimeter Inche	
	Min.	Max.	Min.	Max.
Α	4.9	5.1	.193	.201
A <sub>1</sub>	2.7	2.9	.106	.114
$A_2$	.02	.25	.001	.010
b	1.15	1.45	.045	.057
$b_2$	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
Е	15.85	16.05	.624	.632
E <sub>1</sub>	13.3	13.6	.524	.535
е	5.45 BSC		.215 BS0	
Н	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.2	5 BSC	.01	0 BSC
L4	3.80	4.10	.150	.161